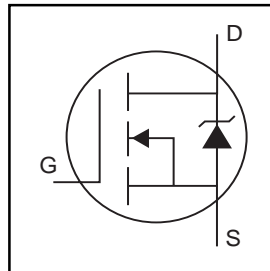


- Advanced Process Technology
- Surface Mount
- Optimized for 4.5V-7.0V Gate Drive
- Ideal for CPU Core DC-DC Converters
- Fast Switching

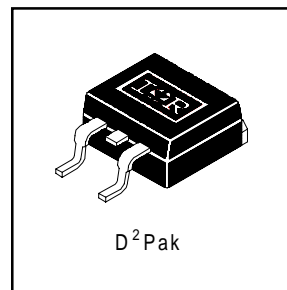


$V_{DSS} = 20V$
$R_{DS(on)} = 0.020\Omega$
$I_D = 39A$

## Description

These HEXFET Power MOSFETs were designed specifically to meet the demands of CPU core DC-DC converters. Advanced processing techniques combined with an optimized gate oxide design results in a die sized specifically to offer maximum efficiency at minimum cost.

The D<sup>2</sup>Pak is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D<sup>2</sup>Pak is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0W in a typical surface mount application.



## Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V$ ⑤	39	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V$ ⑤	25	
$I_{DM}$	Pulsed Drain Current ①⑤	160	
$P_D @ T_C = 25^\circ C$	Power Dissipation	57	W
	Linear Derating Factor	0.45	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 10$	V
$E_{AS}$	Single Pulse Avalanche Energy②⑤	130	mJ
$I_{AR}$	Avalanche Current①	23	A
$E_{AR}$	Repetitive Avalanche Energy①	5.7	mJ
dv/dt	Peak Diode Recovery dv/dt ③⑤	5.0	V/ns
$T_J$	Operating Junction and	-55 to + 150	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds		

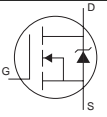
## Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	2.2	°C/W
$R_{\theta JA}$	Junction-to-Ambient ( PCB Mounted, steady-state)**	—	40	

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	20	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$dV_{(BR)DSS}/dT_J$	Breakdown Voltage Temp. Coefficient	—	0.022	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$ ⑤
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.023	m	$V_{GS} = 4.5V, I_D = 23A$ ④
		—	—	0.020		$V_{GS} = 7.0V, I_D = 23A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	0.70	—	—	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$g_{fs}$	Forward Transconductance	21	—	—	S	$V_{DS} = 10V, I_D = 23A$ ⑤
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	25	$\mu A$	$V_{DS} = 20V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 10V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 10V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -10V$
$Q_g$	Total Gate Charge	—	—	31	nC	$I_D = 23A$
$Q_{gs}$	Gate-to-Source Charge	—	—	5.7		$V_{DS} = 16V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	—	13		$V_{GS} = 4.5V$ , See Fig. 6 ④⑤
$t_{d(on)}$	Turn-On Delay Time	—	7.2	—	ns	$V_{DD} = 10V$
$t_r$	Rise Time	—	110	—		$I_D = 23A$
$t_{d(off)}$	Turn-Off Delay Time	—	41	—		$R_G = 9.5\text{m}\Omega, V_{GS} = 4.5V$
$t_f$	Fall Time	—	89	—		$R_D = 2.4\text{m}\Omega$ , ④⑤
$L_S$	Internal Source Inductance	—	7.5	—	nH	Between lead, and center of die contact
$C_{iss}$	Input Capacitance	—	1300	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	520	—		$V_{DS} = 15V$
$C_{rss}$	Reverse Transfer Capacitance	—	190	—		$f = 1.0\text{MHz}$ , See Fig. 5⑤

## Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	39	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ①⑤	—	—	160		
$V_{SD}$	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 23A, V_{GS} = 0V$ ④
$t_{rr}$	Reverse Recovery Time	—	62	94	ns	$T_J = 25^\circ\text{C}, I_F = 23A$
$Q_{rr}$	Reverse Recovery Charge	—	—	110	160	nC $di/dt = 100A/\mu s$ ④⑤
$t_{on}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S+L_D$ )				

### Notes:

① Repetitive rating; pulse width limited by max. junction temperature.

② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.49\text{mH}$   
 $R_G = 25\text{m}\Omega, I_{AS} = 23A$ .

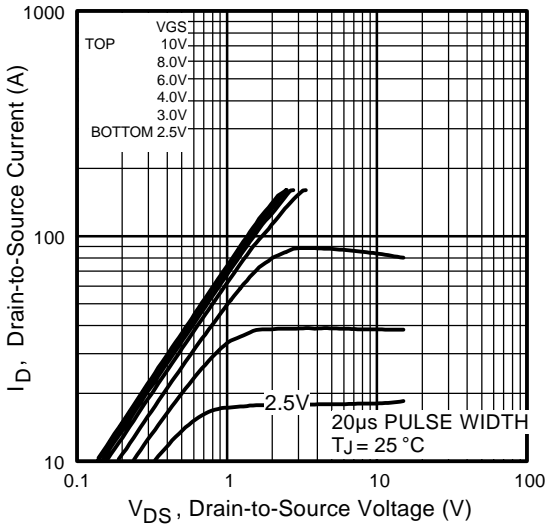
③  $I_{SD} \leq 23A, di/dt \leq 97A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 150^\circ\text{C}$

④ Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$ .

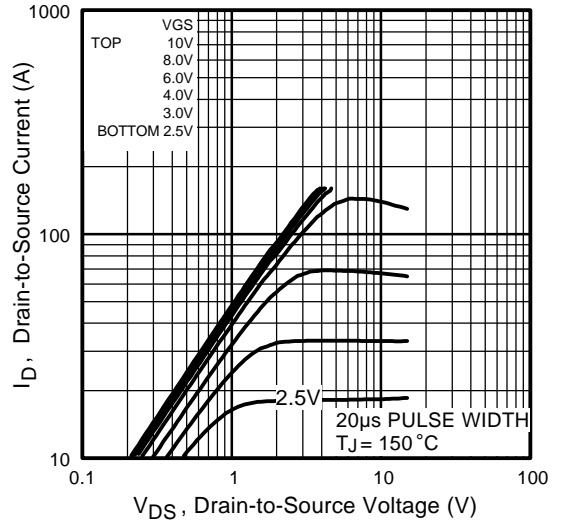
⑤ Uses IRL3302 data and test conditions

\*\* When mounted on FR-4 board using minimum recommended footprint.

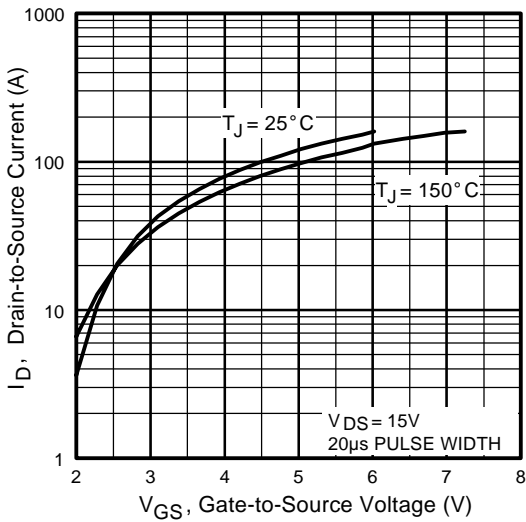
For recommended footprint and soldering techniques refer to application note #AN-994.



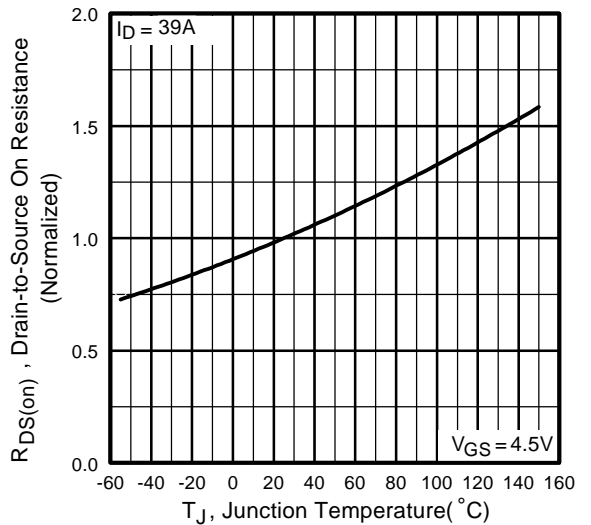
**Fig 1.** Typical Output Characteristics



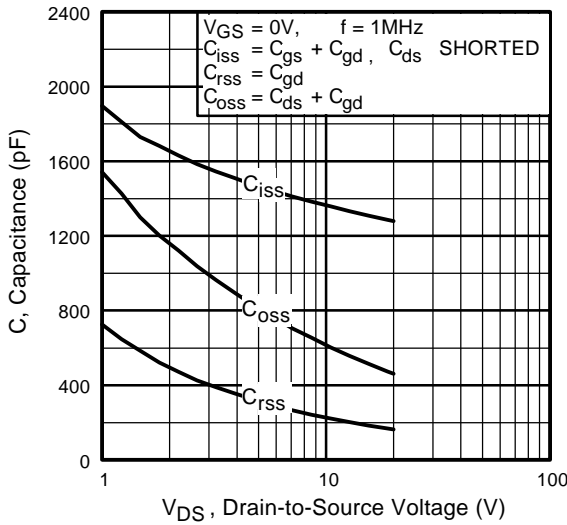
**Fig 2.** Typical Output Characteristics



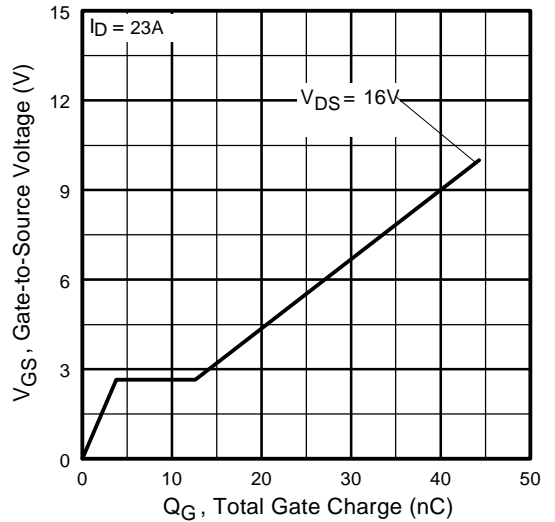
**Fig 3.** Typical Transfer Characteristics



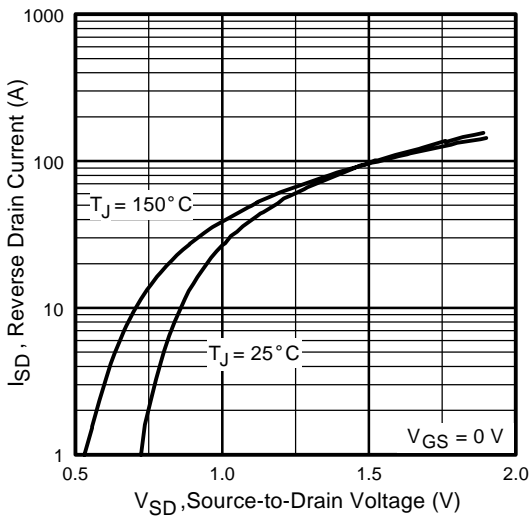
**Fig 4.** Normalized On-Resistance Vs. Temperature



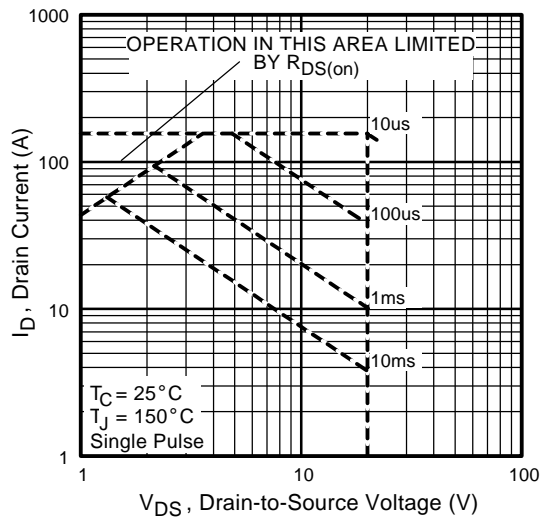
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



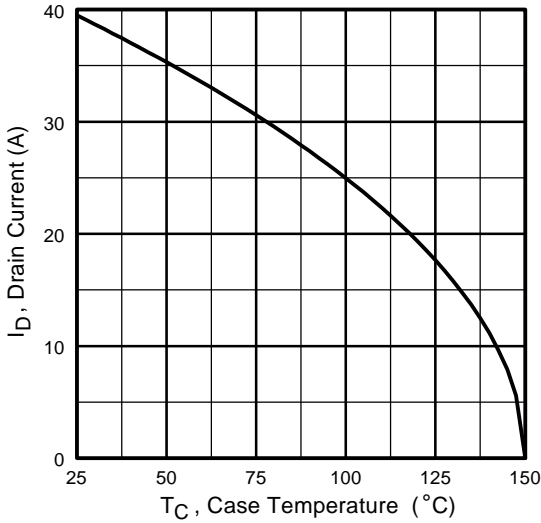
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



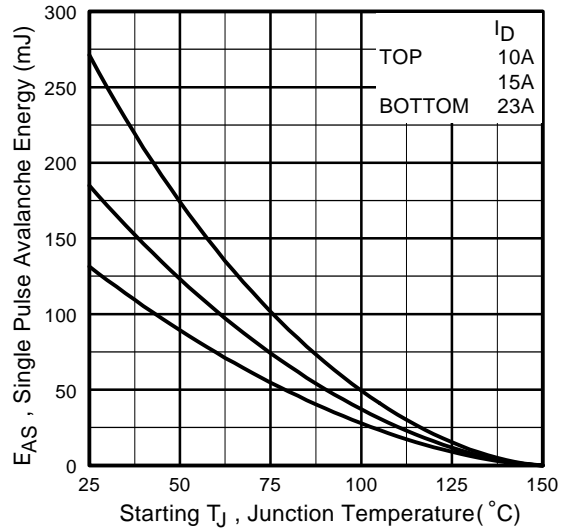
**Fig 7.** Typical Source-Drain Diode Forward Voltage



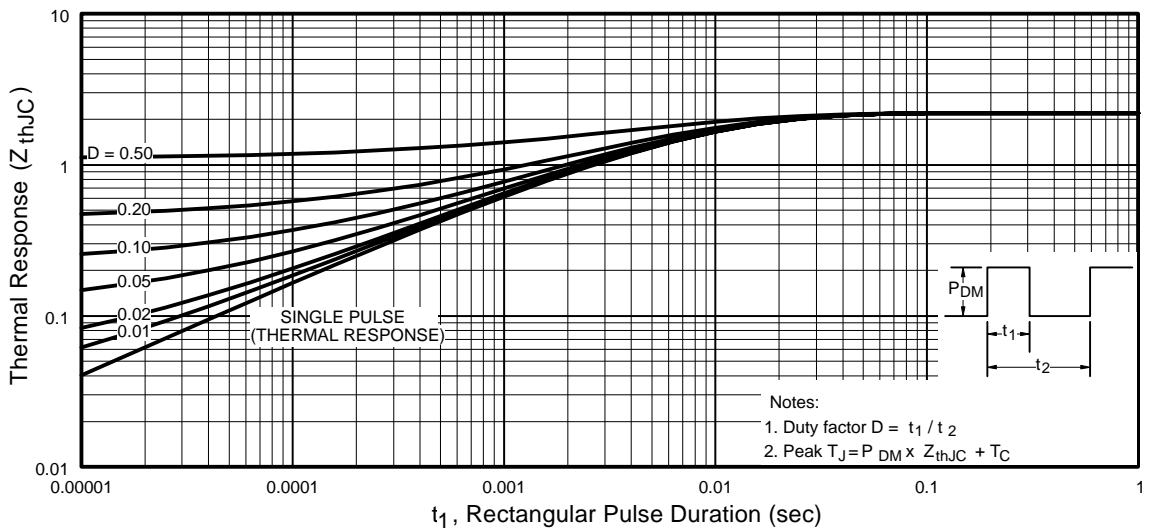
**Fig 8.** Maximum Safe Operating Area



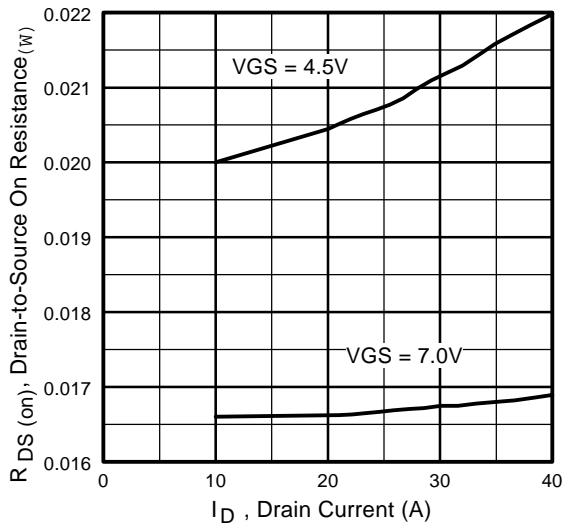
**Fig 9.** Maximum Drain Current Vs. Case Temperature



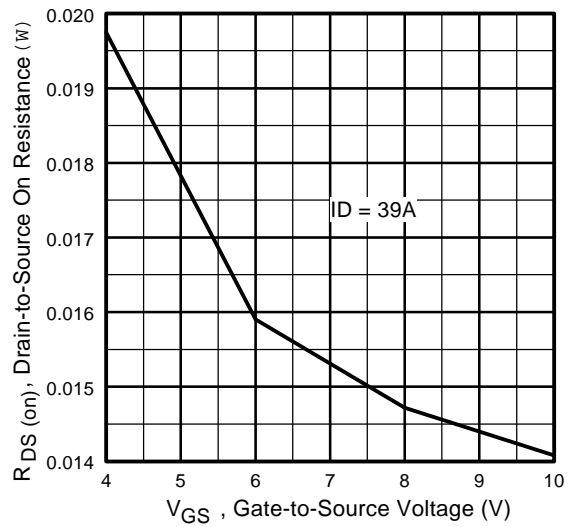
**Fig 10.** Maximum Avalanche Energy Vs. Drain Current



**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case

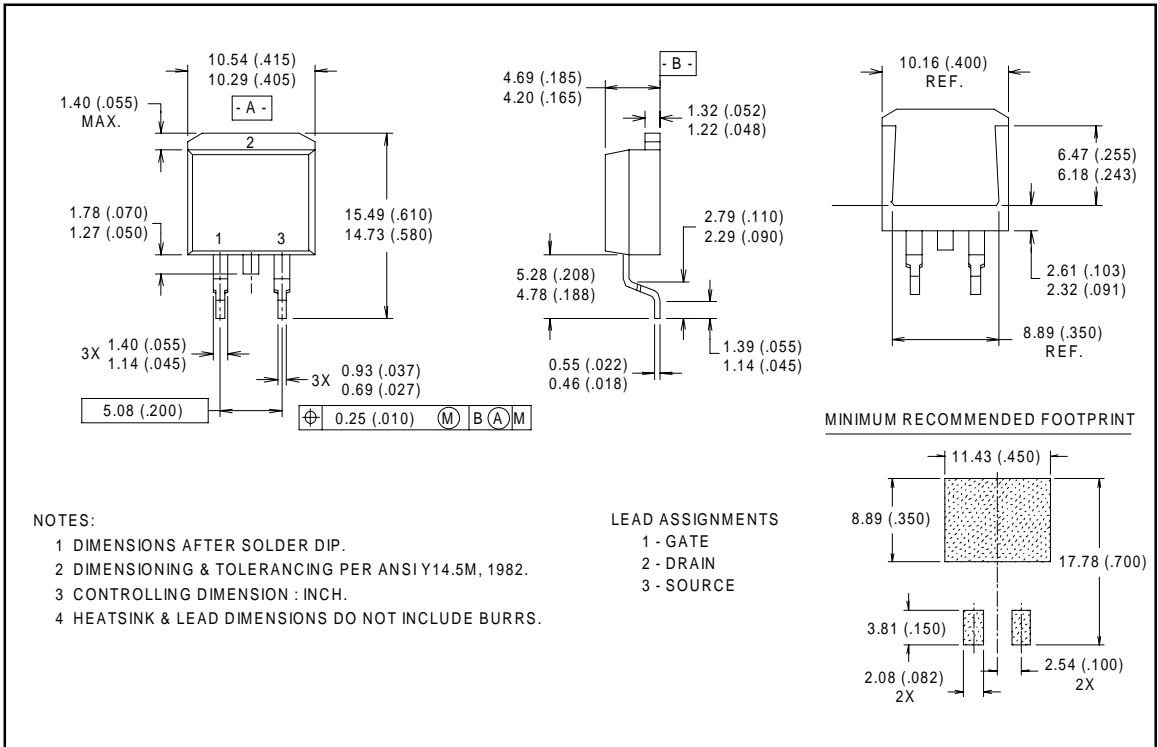


**Fig 12.** On-Resistance Vs. Drain Current



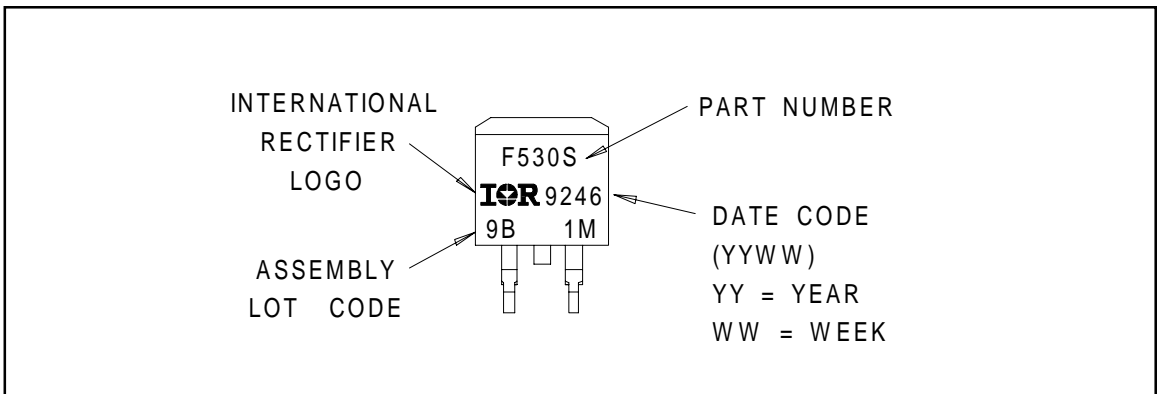
**Fig 13.** On-Resistance Vs. Gate Voltage

## D<sup>2</sup>Pak Package Outline



## Part Marking Information

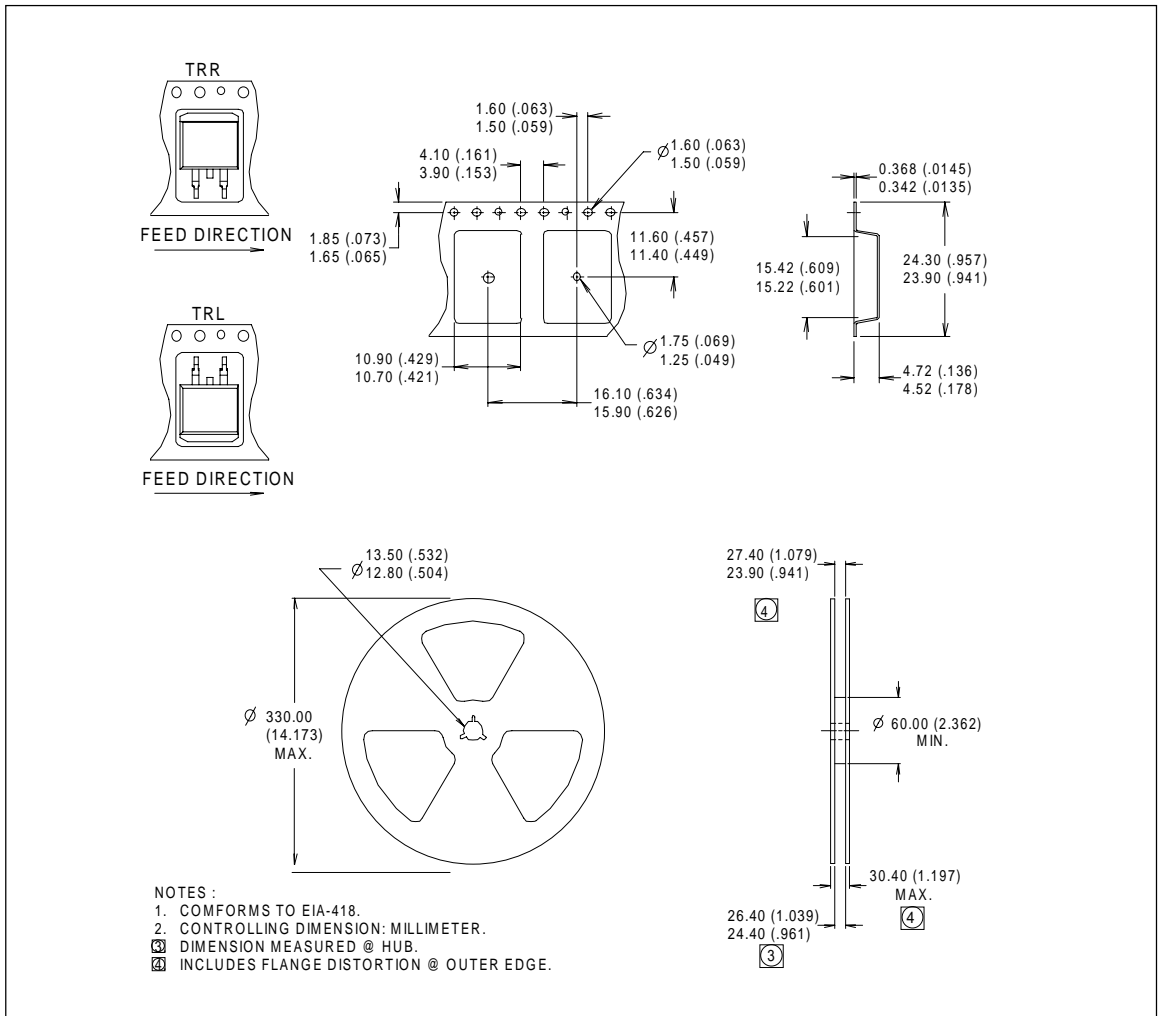
D<sup>2</sup>Pak



# IRL3302S

## Tape & Reel Information

D<sup>2</sup>Pak



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